



P-Ch 150V Fast Switching MOSFETs

Description

The HSH40P15 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

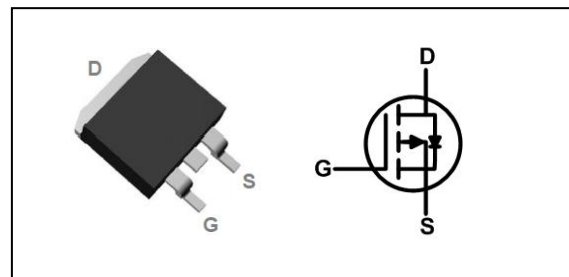
The HSH40P15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-150	V
$R_{DS(ON),typ}$	85	m Ω
I_D	-40	A

TO-263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-150	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ -10V ¹	-40	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, V_{GS} @ -10V ¹	-23	A
I_{DM}	Pulsed Drain Current ²	-120	A
EAS	Single Pulse Avalanche Energy ³	420	mJ
I_{AS}	Avalanche Current	-35	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	100	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.22	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-150	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-15A$	---	85	100	$m\Omega$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5V, I_D=-10A$	---	90	110	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1	-1.65	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-150V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-150V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	-100	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-15A$	---	44	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.6	---	Ω
Q_g	Total Gate Charge	$V_{DS}=-75V, V_{GS}=-10V, I_D=-15A$	---	120	---	nC
Q_{gs}	Gate-Source Charge		---	21	---	
Q_{gd}	Gate-Drain Charge		---	25	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-75V, V_{GS}=-10V, R_G=6\Omega, I_D=-15A$	---	17	---	ns
T_r	Rise Time		---	89	---	
$T_{d(off)}$	Turn-Off Delay Time		---	49	---	
T_f	Fall Time		---	60	---	
C_{iss}	Input Capacitance	$V_{DS}=-75V, V_{GS}=0V, f=1\text{MHz}$	---	8600	---	pF
C_{oss}	Output Capacitance		---	155	---	
C_{rss}	Reverse Transfer Capacitance		---	116	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-40	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-75V, V_{GS}=-10V, L=0.1mH, I_{AS}=-35A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

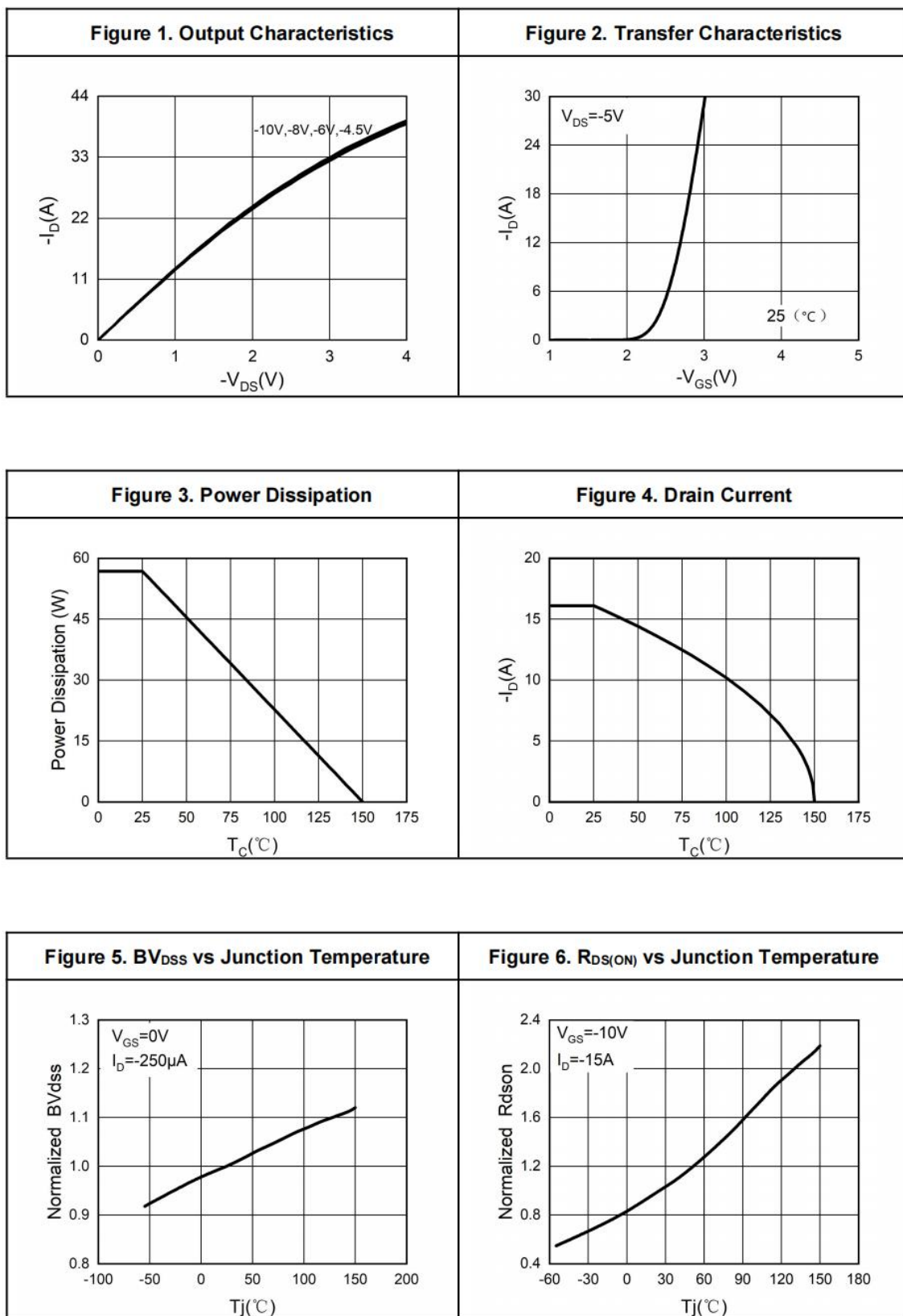




Figure 7. Gate Charge Waveforms

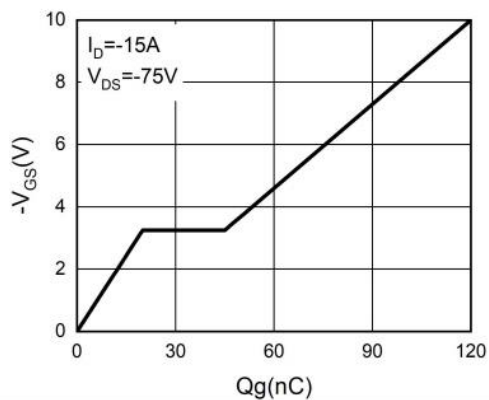


Figure 8. Capacitance

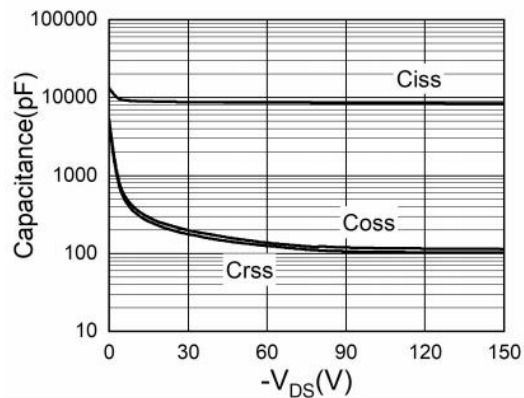


Figure 9. Body-Diode Characteristics

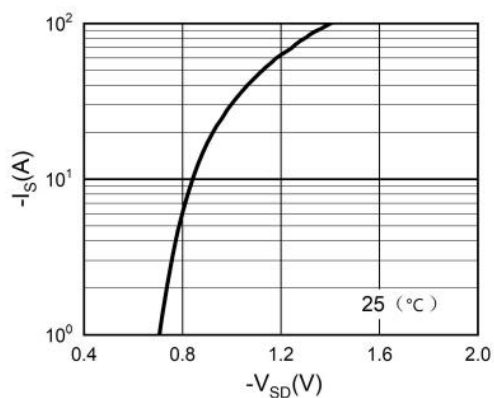
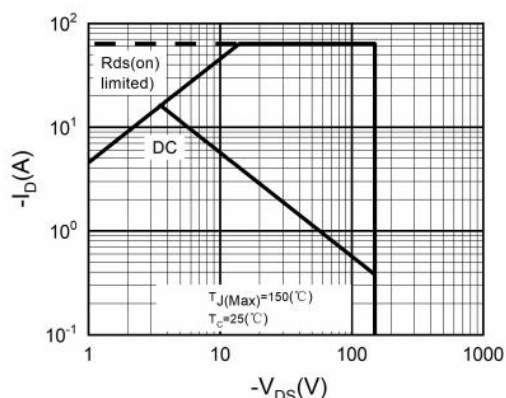


Figure 10. Maximum Safe Operating Area





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